

**AMENDMENTS TO THE CLAIMS**

**This listing of claims will replace all prior versions and listings of claims in the application:**

**LISTING OF CLAIMS:**

Claims 1-27 (canceled).

28. (original): A method for manufacturing a gallium nitride-based compound semiconductor light-emitting device comprising  
(a) forming an n-type semiconductor layer of a gallium nitride-based compound semiconductor, a light-emitting layer of a gallium nitride-based compound semiconductor and a p-type semiconductor layer of a gallium nitride-based compound semiconductor on a substrate in this order,

(b) providing a positive electrode and a negative electrode, which comprises a bonding pad layer and a contact metal layer, on the p-type semiconductor layer and the n-type semiconductor layer, respectively;

wherein the contact metal layer is forming through sputtering Cr or a Cr alloy on the n-type semiconductor layer to attain Ohmic contact without performing annealing.

29. (canceled).